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November 2013

FQPF13N06L

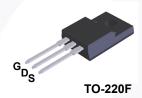
N-Channel QFET[®] MOSFET 60 V, 10 A, 110 m Ω

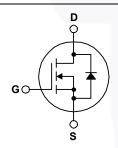
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 10 A, 60 V, $R_{DS(on)}$ = 110 m Ω (Max.) @ V_{GS} = 10 V, I_D = 5 A
- Low Gate Charge (Typ. 4.8 nC)
- Low Crss (Typ. 17 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQPF13N06L	Unit
V_{DSS}	Drain-Source Voltage		60	V
I_D	Drain Current - Continuous (T _C = 25°C)		10	А
	- Continuous (T _C = 100°	°C)	7.1	А
I _{DM}	Drain Current - Pulsed	(Note 1)	40	Α
V_{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	90	mJ
I _{AR}	Avalanche Current	(Note 1)	10	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	2.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		7.0	V/ns
P _D	Power Dissipation (T _C = 25°C)		24	W
	- Derate above 25°C		0.16	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQPF13N06L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	6.20	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF13N06L	FQPF13N06L	TO-220F	Tube	N/A	N/A	50 units

Flectrical Characteristics

Parameter	Test Conditions	Min	Тур	Max	Unit
aracteristics					
Drain-Source Breakdown Voltage	Voltage $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.05		V/°C
7 0 1 1/1 5 1 0 1	V _{DS} = 60 V, V _{GS} = 0 V			1	μА
Zero Gate Voltage Drain Current	V _{DS} = 48 V, T _C = 150°C			10	μΑ
Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
aracteristics					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V
Static Drain-Source	V _{GS} = 10 V, I _D = 5 A		0.088	0.11	
On-Resistance $V_{GS} = 5 \text{ V}, I_D = 5 \text{ A}$			0.110	0.14	Ω
Forward Transconductance	V _{DS} = 25 V, I _D = 5 A		5.5		S
Input Capacitance	V = 25 V V = 0 V		270	350	pF
	f = 1.0 MHz				pF
			17	23	pF
ing Characteristics					-
Turn-On Delay Time	V _{DD} = 30 V I _D = 6.8 A		8	25	ns
Turn-On Rise Time	22		90	190	ns
Turn-Off Delay Time			20	50	ns
Turn-Off Fall Time	(Note 4)		40	90	
			. •	30	ns
Total Gate Charge	V _{DS} = 48 V, I _D = 13.6 A,		4.8	6.4	
	V _{DS} = 48 V, I _D = 13.6 A, V _{GS} = 5 V		_		nC
Total Gate Charge			4.8	6.4	nC nC
Total Gate Charge Gate-Source Charge	V _{GS} = 5 V (Note 4)		4.8 1.6	6.4	ns nC nC
Total Gate Charge Gate-Source Charge Gate-Drain Charge	V _{GS} = 5 V (Note 4)		4.8 1.6	6.4	nC nC
Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar	V _{GS} = 5 V (Note 4) nd Maximum Ratings ode Forward Current		4.8 1.6 2.7	6.4	nC nC
Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics and Maximum Continuous Drain-Source Diode	V _{GS} = 5 V (Note 4) nd Maximum Ratings ode Forward Current		4.8 1.6 2.7	6.4	nC nC nC
	Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse aracteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ μA}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$, Referenced to 25°C Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$ Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse $V_{GS} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -20 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \text{ μA}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}$, $I_D = 5 \text{ A}$ ic Characteristics $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $V_{CS} =$	$\begin{array}{ c c c c } \hline Drain-Source Breakdown Voltage & V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A} & 60 \\ \hline Breakdown Voltage Temperature & I_D = 250 \mu\text{A}, \text{ Referenced to } 25^{\circ}\text{C} & \\ \hline Zero Gate Voltage Drain Current & V_{DS} = 60 \text{ V, } V_{GS} = 0 \text{ V} & \\ \hline V_{DS} = 48 \text{ V, } T_C = 150^{\circ}\text{C} & \\ \hline Gate-Body Leakage Current, Forward & V_{GS} = 20 \text{ V, } V_{DS} = 0 \text{ V} & \\ \hline Gate-Body Leakage Current, Reverse & V_{GS} = -20 \text{ V, } V_{DS} = 0 \text{ V} & \\ \hline \textbf{Gate-Body Leakage Current, Reverse} & V_{DS} = -20 \text{ V, } V_{DS} = 0 \text{ V} & \\ \hline \textbf{aracteristics} & & & & & & & & & & & & & & & & & & &$	$\begin{array}{ c c c c } \hline Drain-Source Breakdown Voltage & V_{GS}=0\ V,\ I_D=250\ \mu A & 60 & \\ \hline Breakdown Voltage Temperature & I_D=250\ \mu A,\ Referenced to 25°C & & 0.05 \\ \hline Zero Gate Voltage Drain Current & V_{DS}=60\ V,\ V_{GS}=0\ V & & \\ \hline Zero Gate Voltage Drain Current & V_{DS}=48\ V,\ T_C=150°C & & \\ \hline Gate-Body Leakage Current,\ Forward & V_{GS}=20\ V,\ V_{DS}=0\ V & & \\ \hline Gate-Body Leakage Current,\ Reverse & V_{GS}=-20\ V,\ V_{DS}=0\ V & & \\ \hline \textbf{Gate Threshold Voltage} & V_{DS}=V_{GS},\ I_D=250\ \mu A & 1.0 & \\ \hline \textbf{Static Drain-Source} & V_{GS}=10\ V,\ I_D=5\ A & & 0.088 \\ \hline On-Resistance & V_{GS}=5\ V,\ I_D=5\ A & & 5.5 \\ \hline \textbf{ic Characteristics} \\ \hline \textbf{Input Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{GS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{GS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & V_{DS}=25\ V,\ V_{DS}=0\ V, & & 270 \\ \hline \textbf{Output Capacitance} & & 0.00\ V,\ V_{DS}=0\ V$	$\begin{array}{ c c c c c } \hline Drain-Source Breakdown Voltage & V_{GS} = 0 \ V, \ I_D = 250 \ \mu A & 60 & & \\ \hline Breakdown Voltage Temperature & I_D = 250 \ \mu A, \ Referenced to 25°C & & 0.05 & \\ \hline Zero \ Gate \ Voltage \ Drain \ Current & V_{DS} = 60 \ V, \ V_{GS} = 0 \ V & & & 1 \\ \hline V_{DS} = 48 \ V, \ T_C = 150°C & & & 10 \\ \hline Gate-Body \ Leakage \ Current, \ Forward & V_{GS} = 20 \ V, \ V_{DS} = 0 \ V & & & 100 \\ \hline Gate-Body \ Leakage \ Current, \ Reverse & V_{GS} = 20 \ V, \ V_{DS} = 0 \ V & & & 100 \\ \hline \textbf{Gate-Body Leakage } & V_{DS} = V_{CS}, \ I_D = 250 \ \mu A & 1.0 & & 2.5 \\ \hline \textbf{Static Drain-Source} & V_{GS} = 10 \ V, \ I_D = 5 \ A & & 0.088 \ 0.11 \\ \hline \textbf{On-Resistance} & V_{GS} = 5V, \ I_D = 5A & & 0.110 \ 0.14 \\ \hline \textbf{Forward Transconductance} & V_{DS} = 25 \ V, \ I_D = 5 \ A & & 5.5 \ \\ \hline \textbf{iic Characteristics} & \\ \hline \textbf{Input Capacitance} & V_{DS} = 25 \ V, \ V_{GS} = 0 \ V, & & 270 \ 350 \\ \hline \textbf{Output Capacitance} & V_{DS} = 25 \ V, \ V_{GS} = 0 \ V, & & 95 \ 125 \\ \hline \textbf{Reverse Transfer Capacitance} & V_{DD} = 30 \ V, \ I_D = 6.8 \ A, & & 8 \ 25 \\ \hline \textbf{Turn-On Delay Time} & V_{DD} = 30 \ V, \ I_D = 6.8 \ A, & & 8 \ 25 \\ \hline \textbf{Turn-On Rise Time} & V_{DD} = 30 \ V, \ I_D = 6.8 \ A, & & 90 \ 190 \\ \hline \textbf{Turn-Off Delay Time} & & 20 \ 50 \\ \hline \end{array}$

Q_{rr}

- Notes:
 1. Repetitive Rating : Pulse width limited by maximum junction temperature.
 2. L = 1.05 mH, I_{AS} = 10 A, V_{DD} = 25 V, R_{G} = 25 Ω , starting T_{J} = 25°C.
 3. I_{SD} ≤ 13.6 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C.
 4. Essentially independent of operating temperature.

Reverse Recovery Charge

nC

45

 $dI_F / dt = 100 A/\mu s$

Typical Characteristics

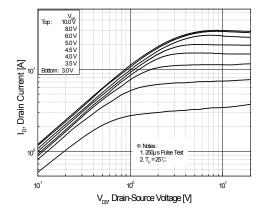


Figure 1. On-Region Characteristics

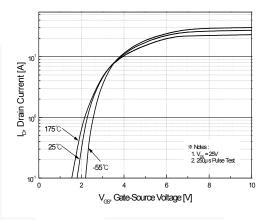


Figure 2. Transfer Characteristics

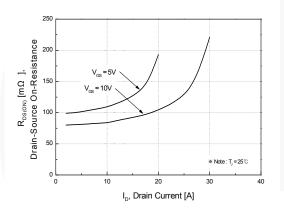


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

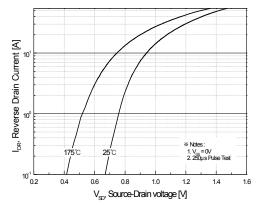


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

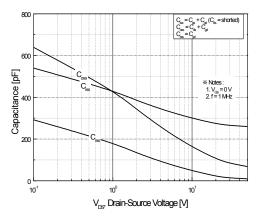


Figure 5. Capacitance Characteristics

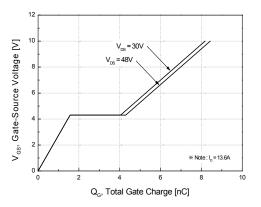


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

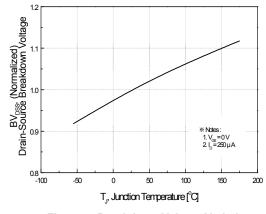


Figure 7. Breakdown Voltage Variation vs. Temperature

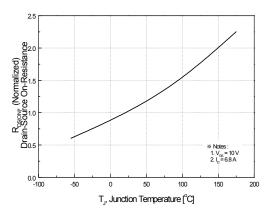


Figure 8. On-Resistance Variation vs. Temperature

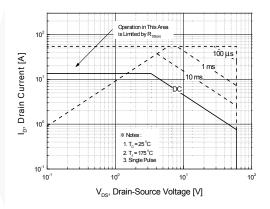


Figure 9. Maximum Safe Operating Area

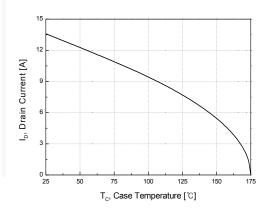


Figure 10. Maximum Drain Current vs. Case Temperature

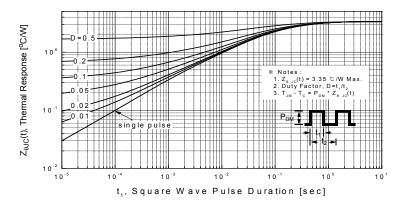


Figure 11. Transient Thermal Response Curve

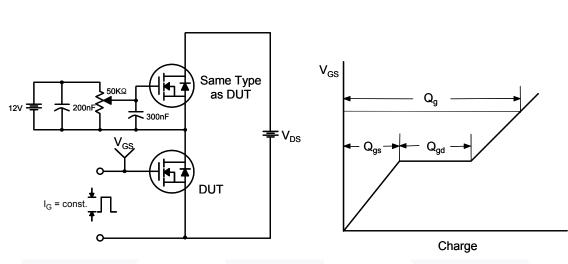


Figure 12. Gate Charge Test Circuit & Waveform

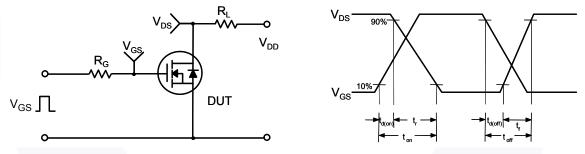


Figure 13. Resistive Switching Test Circuit & Waveforms

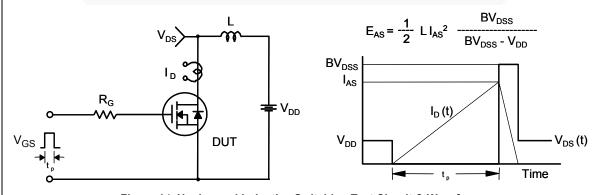
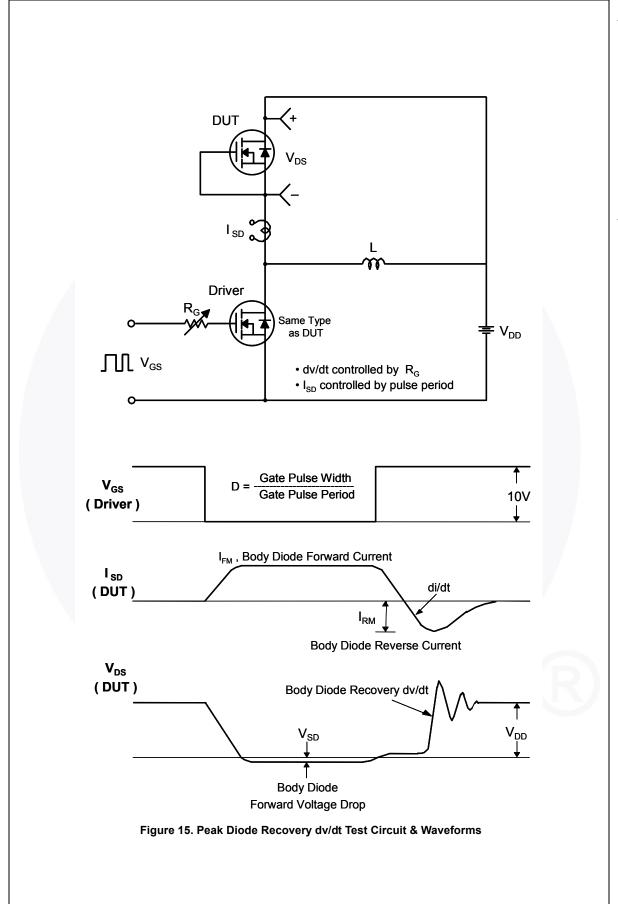


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

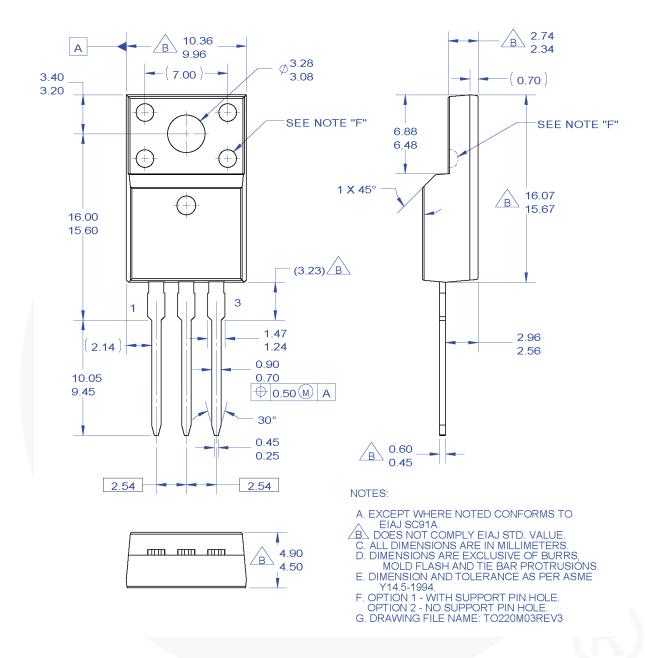


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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